捷多邦,专业PCB打样工厂,24小时加急出货

▲ 面HD74AC366FPEL供应商 NESAS

HD74AC366

Hex Inverter Buffer with 3-State Output

REJ03D0270-0200Z (Previous ADE-205-391 (Z)) Rev.2.00 Jul.16.2004

WWW.DZSC.CO

Features

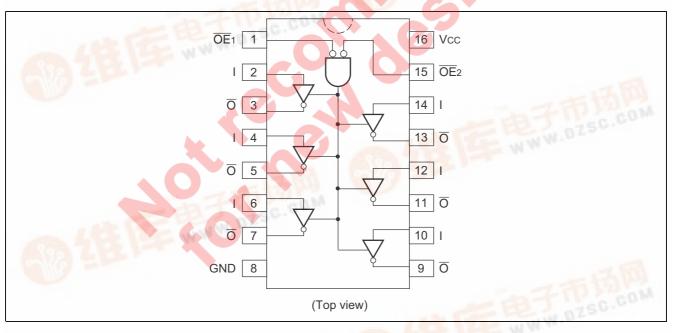
- 3-State Outputs Drive Bus Lines or Buffer Memory Address Registers
- Outputs Source/Sink 24 mA
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74AC366FPEL	SOP-16 pin (JEITA)	FP-16DAV	FP	EL (2,000 pcs/reel)
HD74AC366RPEL	SOP-16 pin (JEDEC)	FP-16DNV	RP	EL (2,500 pcs/reel)

Notes: 1. Please consult the sales office for the above package availability.

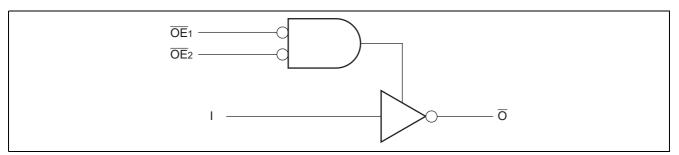
2. The packages with lead-free pins are distinguished from the conventional products by adding V at the end of the package code.

Pin Arrangement





Logic Symbol



Pin Names

- $\overline{OE}_1, \overline{OE}_2$ 3-State Output: Enable Input (Active Low)
- I Inputs
- 0 Outputs

Truth Table

Inputs				Output
OE ₁			5	0
L	L	L		Н
L	L	н		L
Х	Н	X		Z
Н	x	X		Z
 H : High Voltage Level L : Low Voltage Level X : Immaterial Z : High Impedance Absolute Maximum	Ratings	nies		
Item	Symbol	Ratings	Uni	t Condition

- High Voltage Level L : Low Voltage Level
- X : Immaterial
- Z : High Impedance

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Condition	
Supply voltage	V _{cc}	-0.5 to 7	V		
DC input diode current	I _{IK}	-20	mA	$V_1 = -0.5V$	
		20	mA	$V_1 = Vcc+0.5V$	
DC input voltage	V	-0.5 to Vcc+0.5	V		
DC output diode current	I _{ок}	-50	mA	$V_0 = -0.5V$	
		50	mA	$V_{O} = Vcc+0.5V$	
DC output voltage	Vo	-0.5 to Vcc+0.5	V		
DC output source or sink current	I _o	±50	mA		
DC V_{cc} or ground current per output pin	I _{CC} , I _{GND}	±50	mA		
Storage temperature Tstg		–65 to +150	°C		

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Condition
Supply voltage	V _{cc}	2 to 6	V	
Input and Output voltage	V _I , V _O	0 to V _{cc}	V	
Operating temperature	Та	-40 to +85	°C	
Input rise and fall time	tr, tf	8	ns/V	$V_{\rm CC} = 3.0 V$
(except Schmitt inputs)				$V_{\rm CC} = 4.5 \ V$
$V_{\rm IN}$ 30% to 70% $V_{\rm CC}$				V _{CC} = 5.5 V

DC Characteristics

ltem	Sym- bol	Vcc (V)	1	Га = 25°(C	Ta = -40 to +85°C		Unit	Condition
			min.	typ.	max.	min.	max.		
Input Voltage	V _{IH}	3.0	2.1	1.5	—	2.1	—	V	V_{OUT} = 0.1 V or V_{CC} –0.1 V
		4.5	3.15	2.25	_	3.15	_		
		5.5	3.85	2.75	_	3.85	—		
	VIL	3.0	—	1.50	0.9	—	0.9		$V_{OUT} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$
		4.5	—	2.25	1.35	—	1.35		
		5.5	—	2.75	1.65	—	1.65		
Output voltage	V _{OH}	3.0	2.9	2.99	—	2.9	—	V	$V_{IN} = V_{IL} \text{ or } V_{IH}$
		4.5	4.4	4.49	—	4.4	—		I _{OUT} = -50 μA
		5.5	5.4	5.49	—	5.4	—		
		3.0	2.58	—	—	2.48	—		$V_{IN} = V_{IL} \text{ or } V_{IH}$ $I_{OH} = -12 \text{ mA}$
		4.5	3.94	—	—	3.80	—		I _{он} = –24 mA
		5.5	4.94	—	—	4.80	—		I _{OH} = -24 mA
	V _{OL}	3.0	—	0.002	0.1	—	0.1		$V_{IN} = V_{IL} \text{ or } V_{IH}$
		4.5	—	0.001	0.1	—	0.1		I _{OUT} = 50 μA
		5.5	—	0.001	0.1	—	0.1		
		3.0	—	—	0.32	—	0.37		$V_{IN} = V_{IL} \text{ or } V_{IH}$ $I_{OL} = 12 \text{ mA}$
		4.5	—	—	0.32	-	0.37		I _{oL} = 24 mA
		5.5	—	—	0.32		0.37		I _{oL} = 24 mA
Input leakage current	I _{IN}	5.5	_	_	±0.1		±1.0	μA	$V_{IN} = V_{CC}$ or GND
3 State current	I _{oz}	5.5	—	—	±0.5	F.	±5.0	μA	$V_{IN(OE)} = V_{IL}, V_{IH}$
									$V_{IN} = V_{CC}$ or GND
	1	5.5				86	_	m۸	$V_{OUT} = V_{CC}$ or GND
Dynamic output current*	I _{OLD}		-				_	mA mA	$V_{OLD} = 1.1 V$
	I _{OHD}	5.5			-	-75		mA	$V_{OHD} = 3.85 V$
Quiescent supply current	I _{cc}	5.5			8.0	-	80	μA	$V_{IN} = V_{CC}$ or ground

*Maximum test duration 2.0 ms, one output loaded at a time.

AC Characteristics

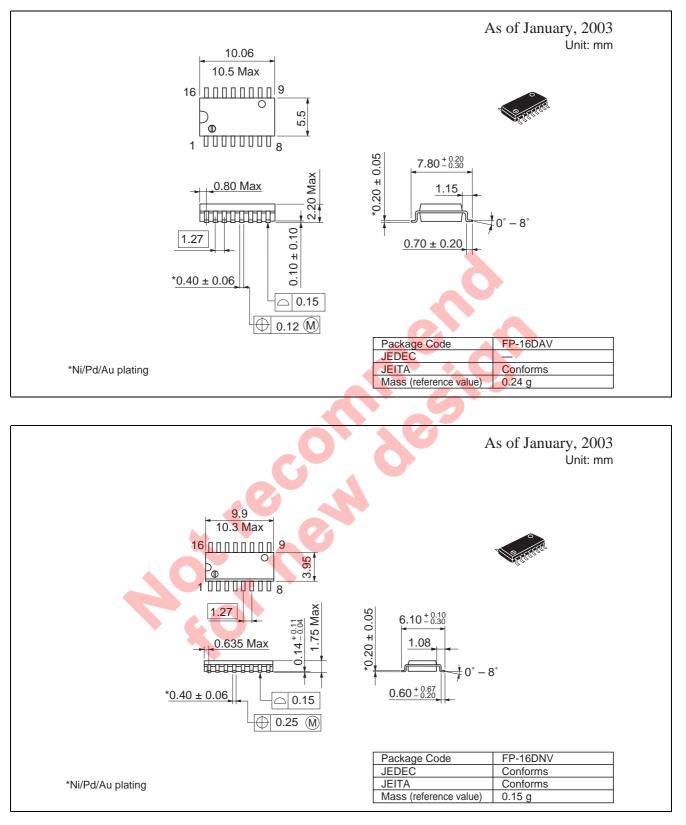
		0	Ta = +25°C C _L = 50 pF				C to +85°C 50 pF	
Item	Symbol	V _{cc} (V)* ¹	Min	Тур	Max	Min	Max	Unit
Propagation delay	t _{PLH}	3.3	1.0	7.0	9.0	1.0	10.0	ns
		5.0	1.0	5.0	7.0	1.0	7.5	
Propagation delay	t _{PHL}	3.3	1.0	7.0	9.0	1.0	10.0	ns
		5.0	1.0	4.5	7.0	1.0	7.5	
Enable time	t _{zH}	3.3	1.0	9.0	13.0	1.0	13.5	ns
		5.0	1.0	7.0	9.5	1.0	10.0	
Enable time	t _{zL}	3.3	1.0	10.0	12.5	1.0	13.5	ns
		5.0	1.0	7.5	9.5	1.0	10.0	
Disable time	t _{HZ}	3.3	1.0	9.5	12.0	1.0	12.5	ns
		5.0	1.0	7.5	10.0	1.0	10.5	
Disable time	t _{LZ}	3.3	1.0	9.0	12.5	1.0	13.5	ns
		5.0	1.0	7.0	10.0	1.0	10.5	

Note: 1. Voltage Range 3.3 is $3.3 \text{ V} \pm 0.3 \text{ V}$ Voltage Range 5.0 is $5.0 \text{ V} \pm 0.5 \text{ V}$

Capacitance

ltem	Symbol	Тур	Unit	Condition
Input capacitance	C _{IN}	4.5	pF	$V_{CC} = 5.5 V$
Power dissipation capacitance	C _{PD}	40.0	pF	$V_{\rm CC} = 5.0 \text{ V}$

Package Dimensions



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